

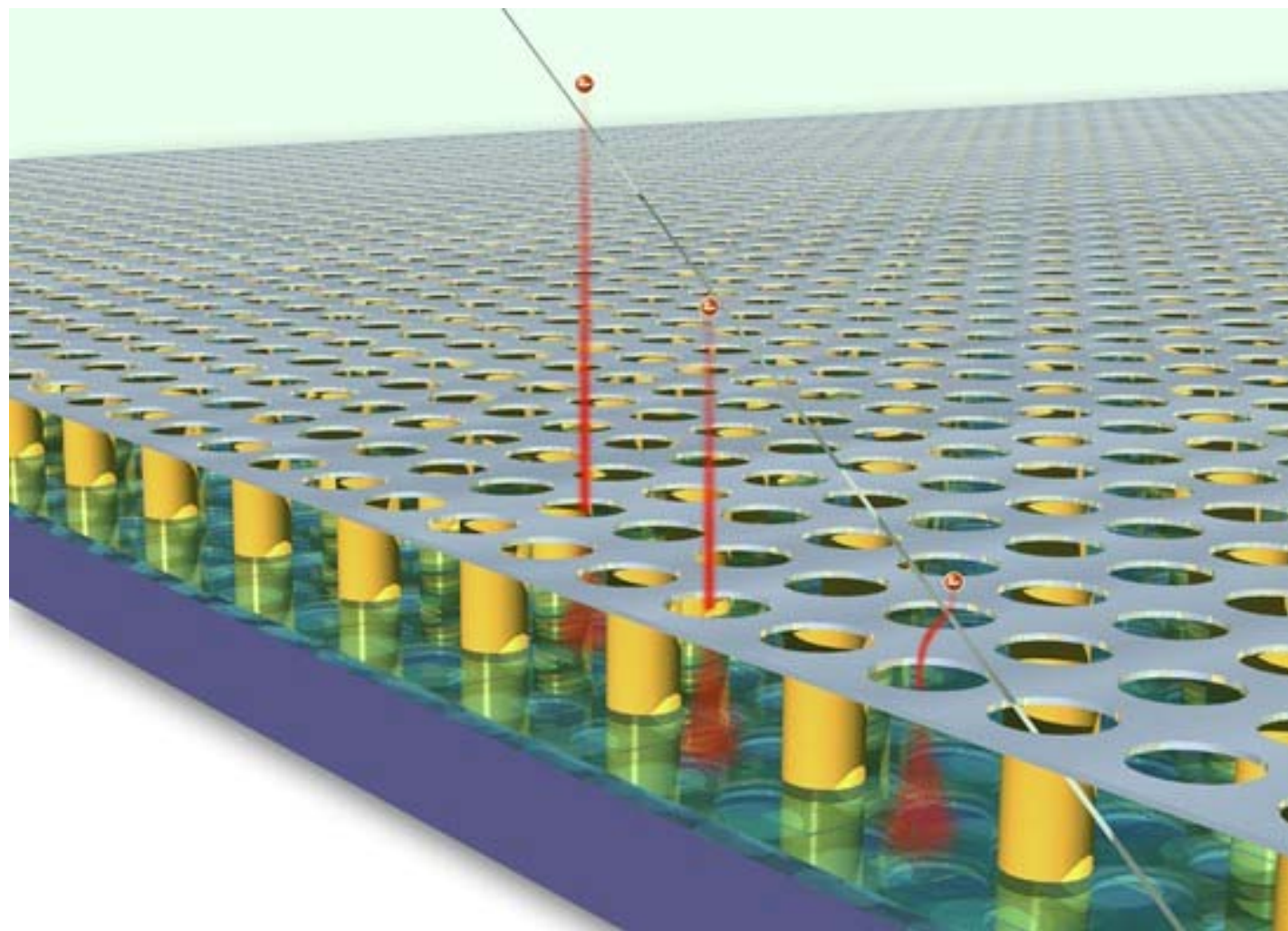
Simulation of Gossip MPGD: Analysis of Tracks in a 1 mm Thick Gas Layer

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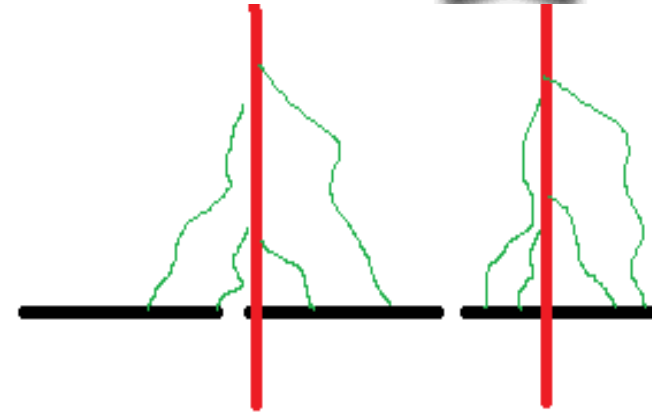
Introduction



Configuration

- GARFIELD for Drift Gap, MCGossip
- HEED (gas parameters)
- CO₂ (50%), DME (50%), T= 293K, P= 1atm
- Drift Gap 1 mm, Avalanche Gap 50 μm
- Diffusion 98.5 $\mu\text{m}/\sqrt{\text{cm}}$ (L), 114.5 $\mu\text{m}/\sqrt{\text{cm}}$ (T)
- Sample: 1000 muons (10 GeV MCGossip, 1 GeV Garfield)
- Drift voltage -700 V
- Grid -400 V
- Chip ground
- No Chip MC used (yet)
- Drift velocity: 55,6 $\mu\text{m}/\text{ns}$

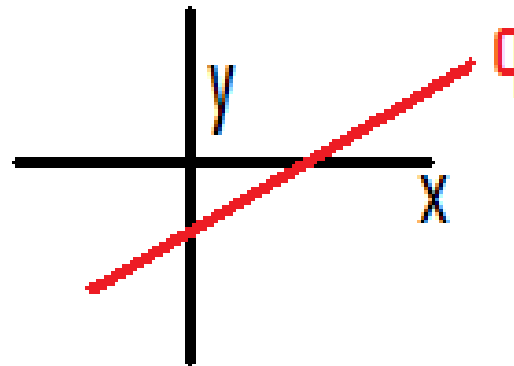
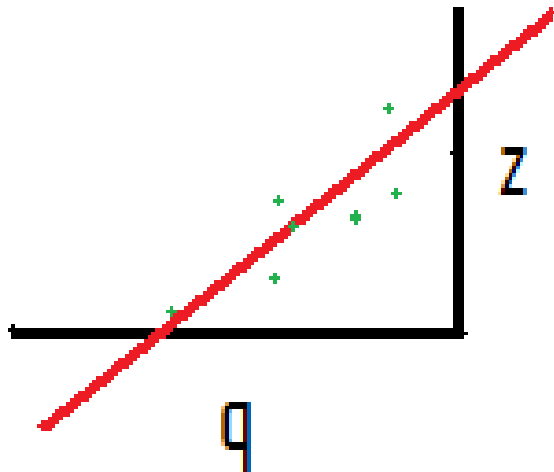
Variables



- Pitch
- Time resolution
- Angle muon track wrt chip (ϕ)

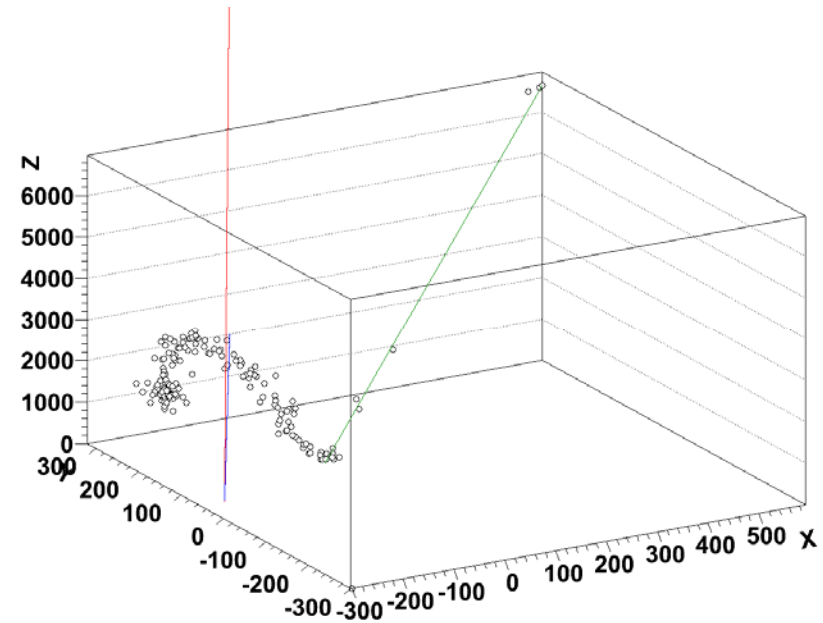
Goal: optimize variables

- Position muon on pixel ($-0.125 < x, y < 0.125$ mm)
- Angle muon track wrt x-axis ($0 < \theta < \pi/4$, a-symmetry)



Setup MC Simulation

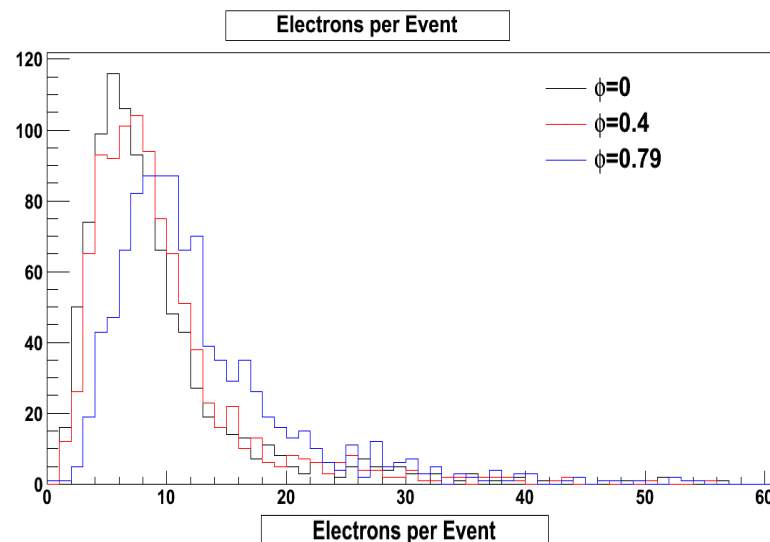
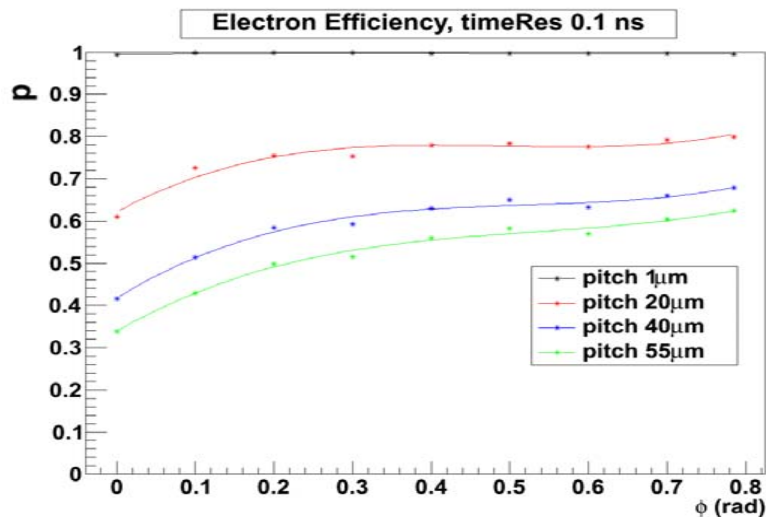
- Delta rays disturb fitting procedure
-> perfect analysis or switch off delta rays.
- Samples without delta rays show limits
- In an experiment a muon travels through multiple gossips: constrained ϕ and θ .
- From Garfield exact locations (x,y,z) -> Bin in pixels (nx,ny,nz)
- Choice pitches: 1×1 , 20×20 , 40×40 , $55 \times 55 \mu\text{m}$
- Choice Time Res: .1, .5, 1.0, 1.5, 1.8, 2.0 ns



Setup Analysis

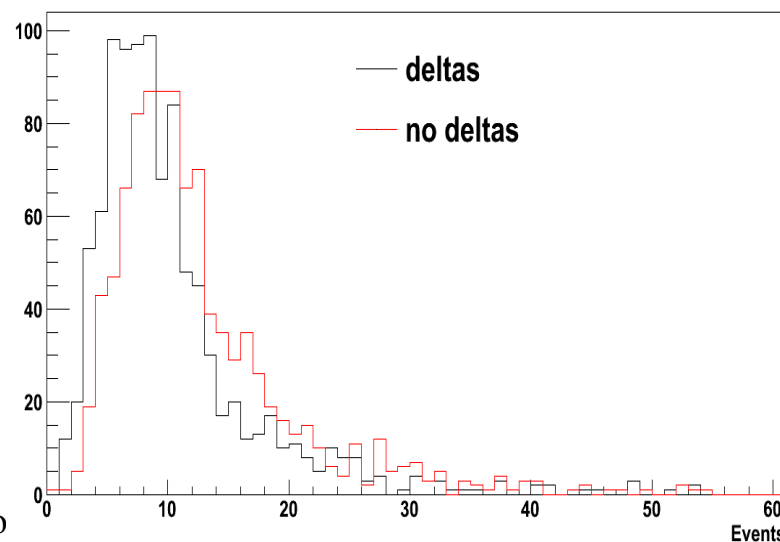
- ROOT
- 3D line Fit procedure MINUIT
- Weight electrons \sim Transverse Diffusion
- Fit 3D line through n_x, n_y, n_z per event.
- Constrained \rightarrow position where track hits chip (x_0, y_0)
- Unconstrained \rightarrow angles ϕ, θ, x_0 and y_0
- Resolution: $x_{0 \text{ garfield}} - x_{0 \text{ fit}}$ for $N_e > 1$

Results



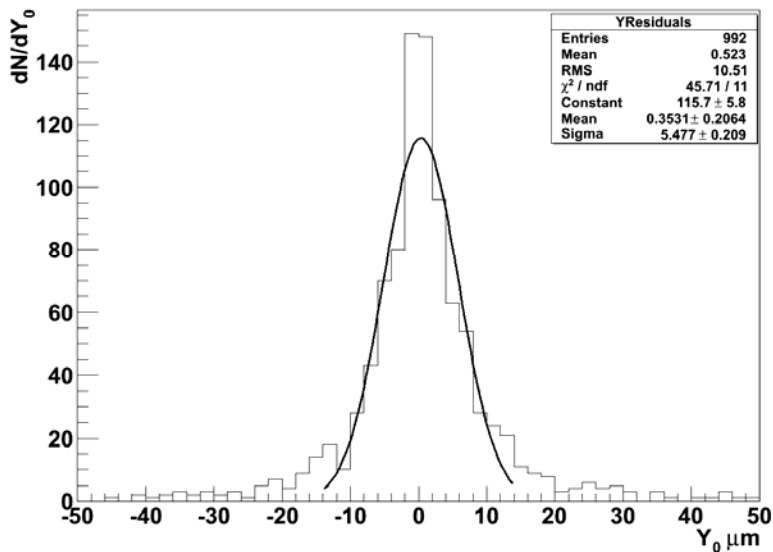
- Electrons per event ~ 5 (small angles) ~ 10 (large angles)

- Electrons efficiency drops to 30% at large pitch and small angles

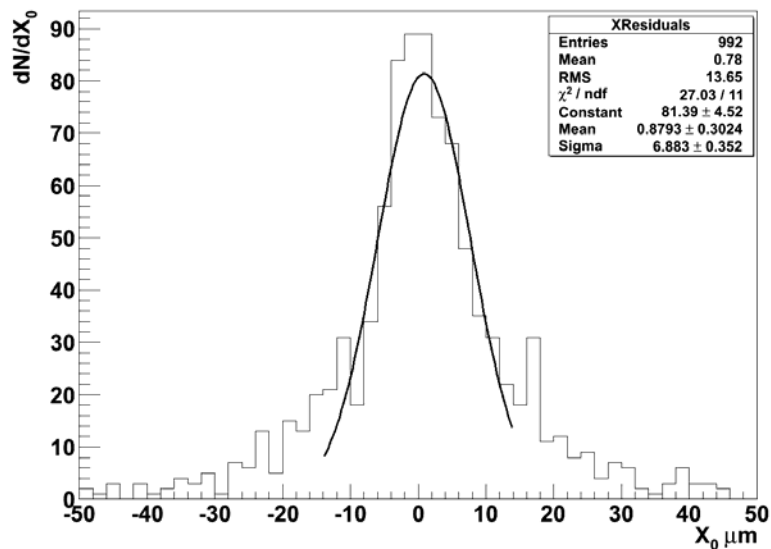


Results

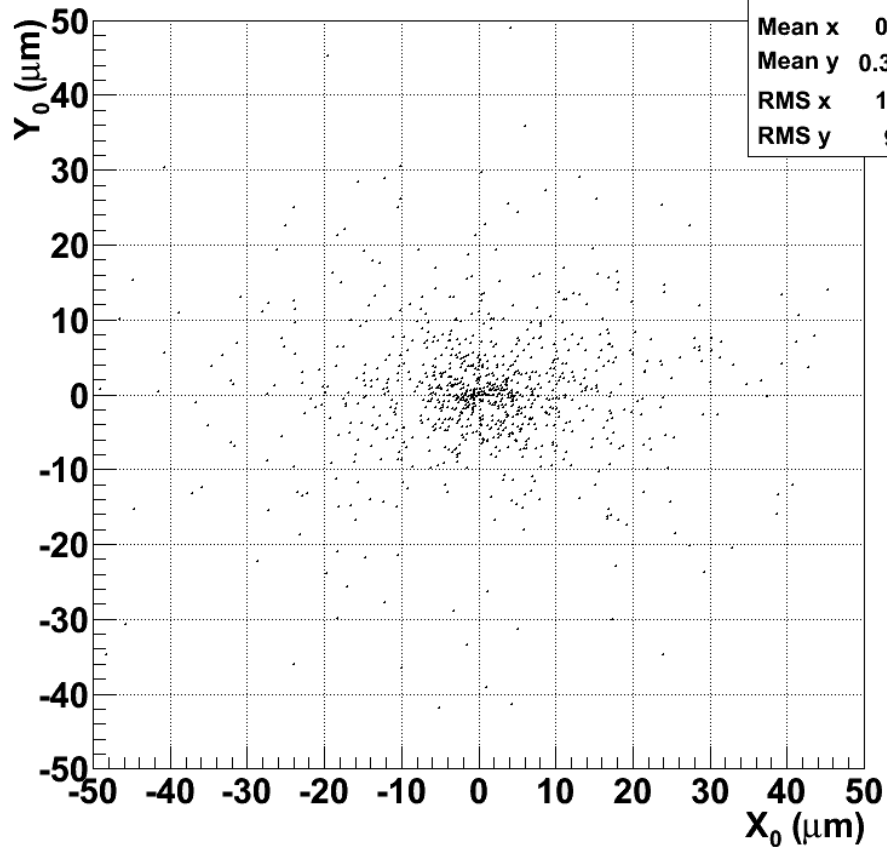
Y_0 Residuals



X_0 Residuals

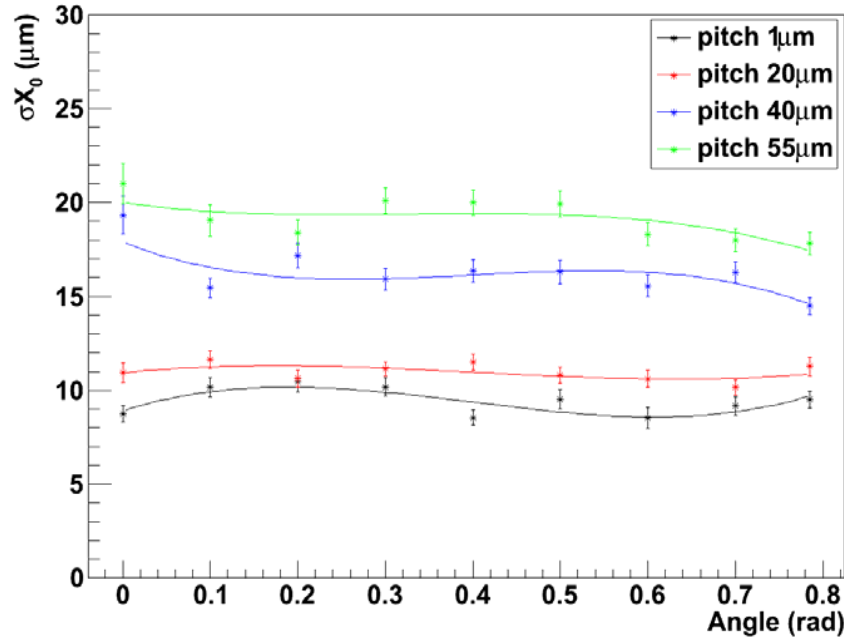


Y_0, X_0 Residuals

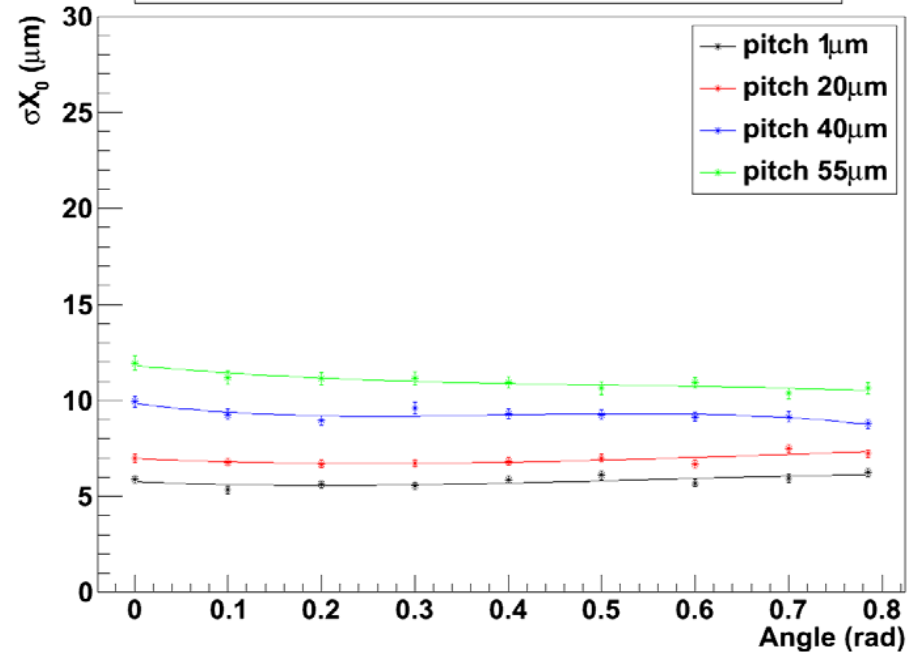


Results

X_0 Residuals, timeRes 0.1 ns, >1 electrons

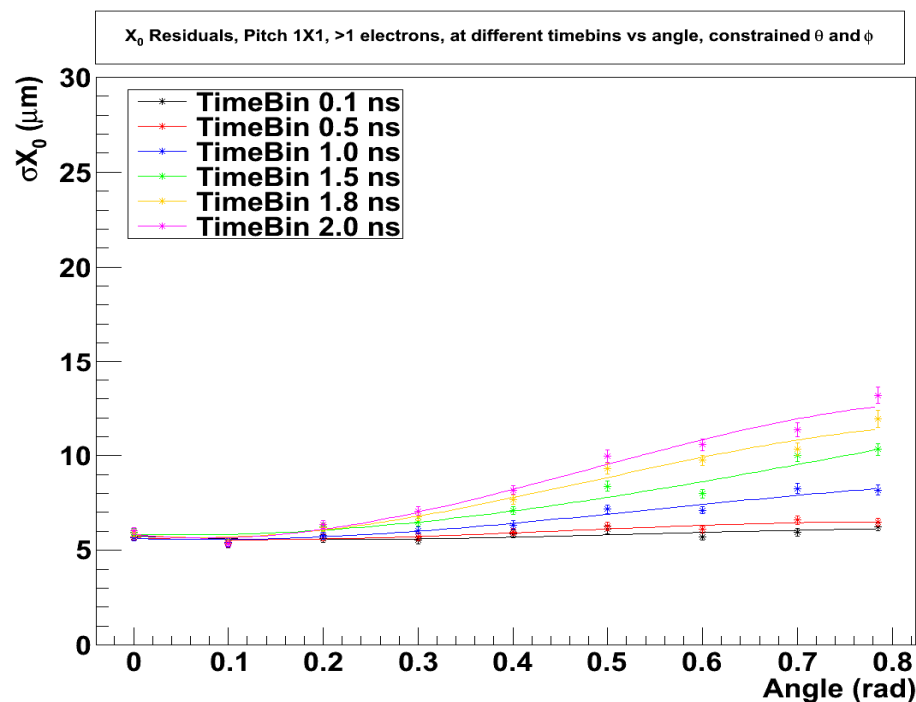
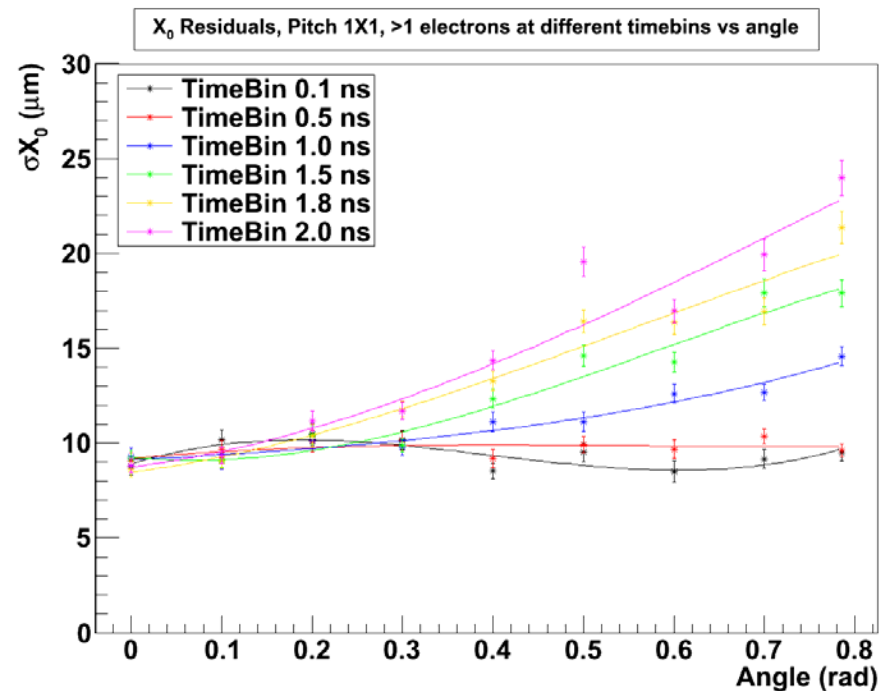


X_0 Residuals, timeRes 0.1 ns, >1 electrons, constrained ϕ and θ



• $\sigma_{\text{constr}} < \sigma_{\text{constr}}$ as expected and stays constant for TimeRes=0.1 ns, for constrained ϕ and θ (better resolution for longer tracks canceled by Z-diffusion)

Results



-Worsen TimeRes dominates resolution at large angles, but resolution stays small at constrained θ and ϕ .

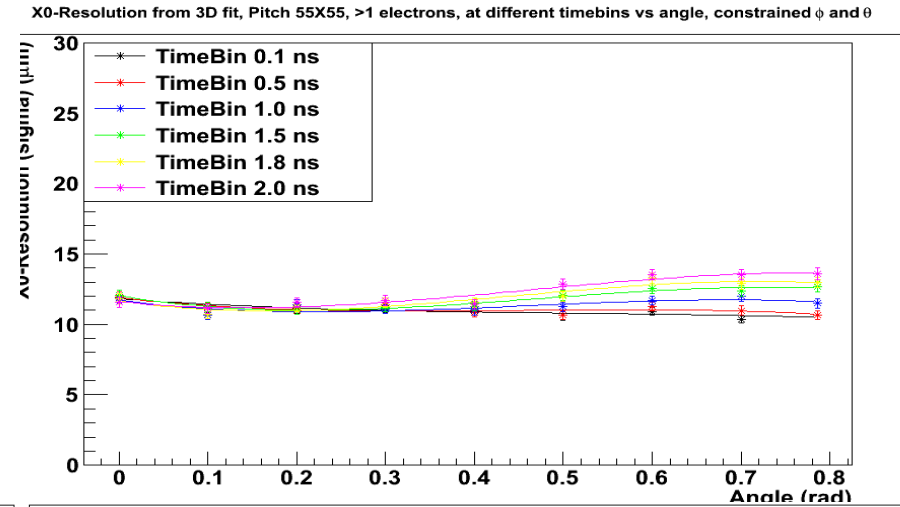
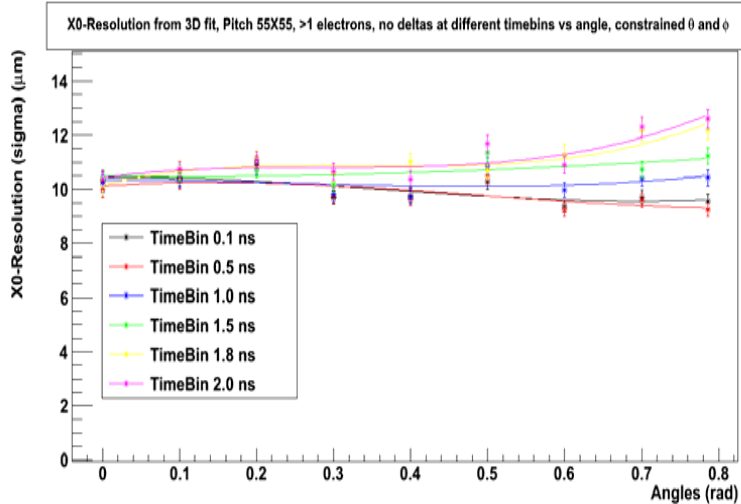
Results MC for 55x55 um



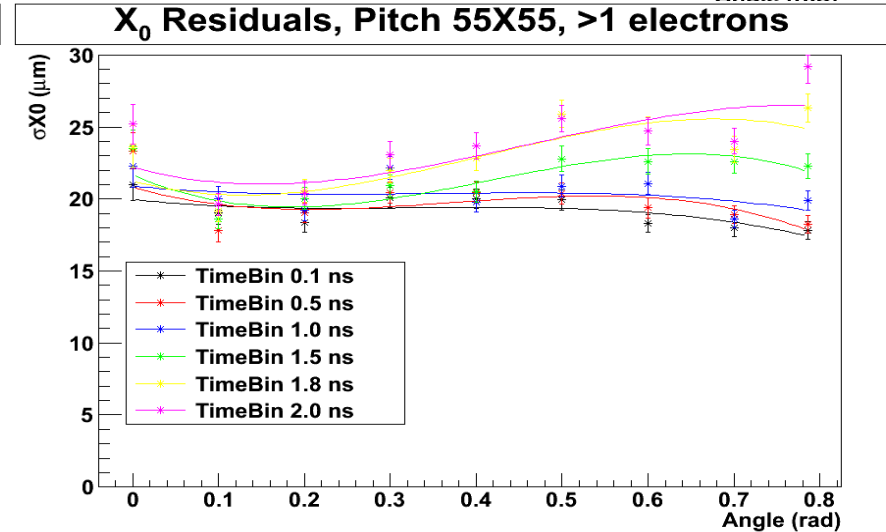
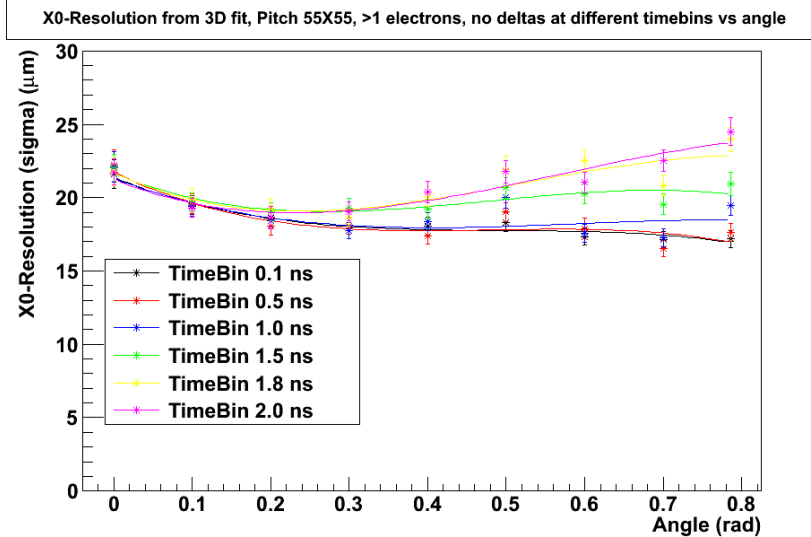
No Deltas

Deltas

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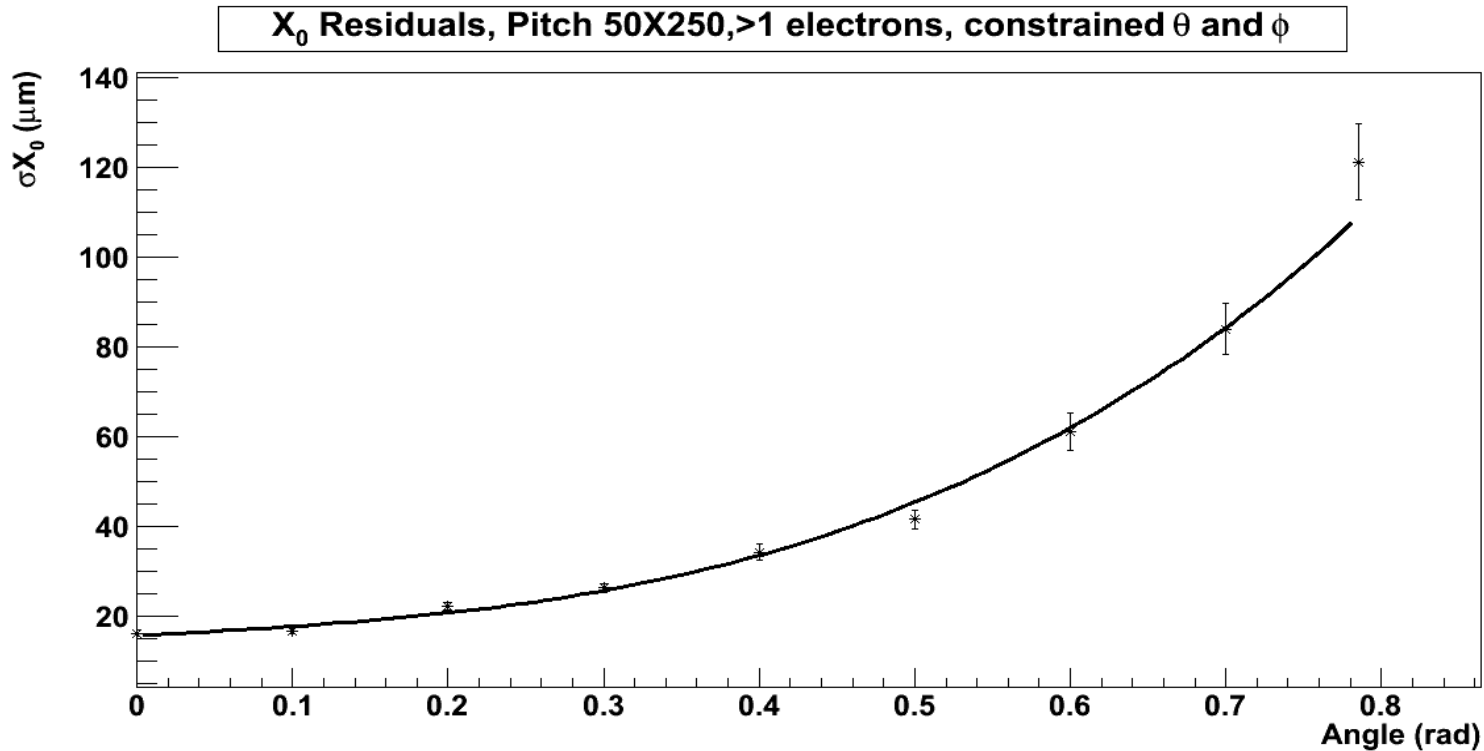
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Conclusions

- Time resolution dominates at large angles
Best Performance at $\phi = 0.1-0.2$ rad
- Constrained angles improve resolution ~ 2 times
- Good analysis (excluding deltas) few μm improvement
- Physical limit GOSSIP $\sigma \sim 5 \mu\text{m}$ (with this settings)
- Expected resolution current timepix
 $\sim 10-11 \mu\text{m}$ (constrained) @ $\phi = 0.1-0.2$ rad

Fe-I4 results



- Fe-I4 50X250, ATLAS chip, for the no delta case

To Do

- Verify results in test beam for current TimePix
- Develop analysis method to extract deltas
- Add electronics + signal development to simulation (distinguish two hits on one pixel?)
- Find Gas with smaller diffusion?